



STW55NM60N

N-channel 600 V, 0.047 Ω , 51 A, MDmesh™ II Power MOSFET
TO-247

Features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)} max	I _D
STW55NM60N	650 V	< 0.060 Ω	51 A

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Application

- Switching applications

Description

This series of devices is designed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

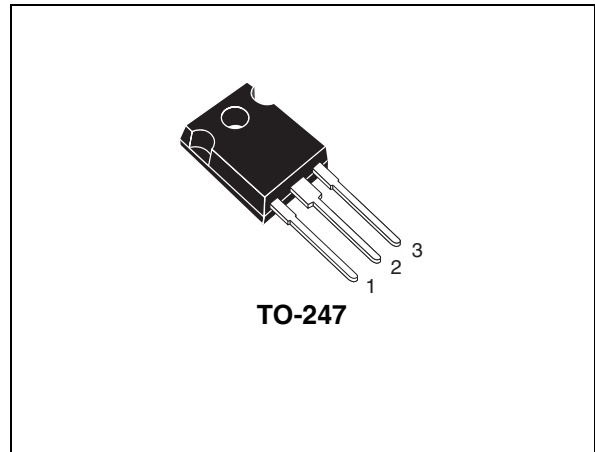


Figure 1. Internal schematic diagram

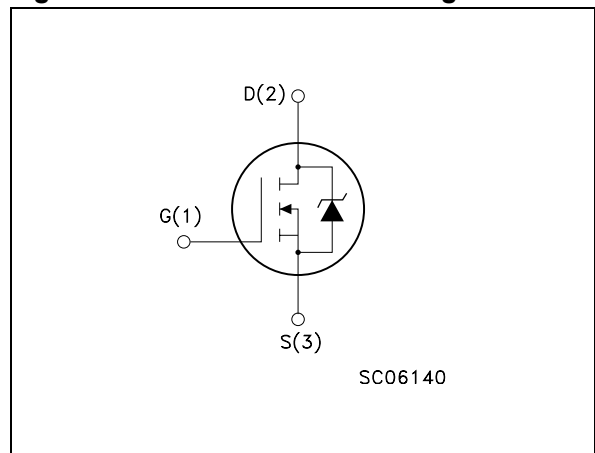


Table 1. Device summary

Order code	Marking	Package	Packaging
STW55NM60N	W55NM60N	TO-247	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	600	V
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	51	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	32	A
$I_{DM}^{(1)}$	Drain current (pulsed)	204	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	350	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 51$ A, $di/dt \leq 400$ A/ μs , $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.36	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C/W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	15	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50$ V)	1600	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1mA, V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain source voltage slope	$V_{DD}= 480 V, I_D = 51 A,$ $V_{GS} = 10 V$		30		V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}, @125^{\circ}C$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 25.5 A$		0.047	0.060	Ω

1. Characteristic value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS}=15 V, I_D = 25.5 A$		45		S
C_{iss}	Input capacitance	$V_{DS} = 50 V, f = 1 MHz,$ $V_{GS} = 0$		5800		pF
C_{oss}	Output capacitance			300		pF
C_{rss}	Reverse transfer capacitance			30		pF
$C_{oss eq.}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0 \text{ to } 480 V$		900		pF
Q_g	Total gate charge	$V_{DD} = 480 V, I_D = 51 A,$ $V_{GS} = 10 V,$ <i>(see Figure 15)</i>		190		nC
Q_{gs}	Gate-source charge			30		nC
Q_{gd}	Gate-drain charge			90		nC
R_g	Gate input resistance	f=1 MHz gate DC bias=0 Test signal level = 20 mV open drain		2.5		Ω

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2. $C_{oss eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 25.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14)		40		ns
t_r	Rise time			30		ns
$t_{d(off)}$	Turn-off delay time			225		ns
t_f	Fall time			70		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				51	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				204	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 25.5\text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 51\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ (see Figure 16)		600		ns
Q_{rr}	Reverse recovery charge			15		μC
I_{RRM}	Reverse recovery current			51		A
t_{rr}	Reverse recovery time	$I_{SD} = 51\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16)		750		ns
Q_{rr}	Reverse recovery charge			18		μC
I_{RRM}	Reverse recovery current			51		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

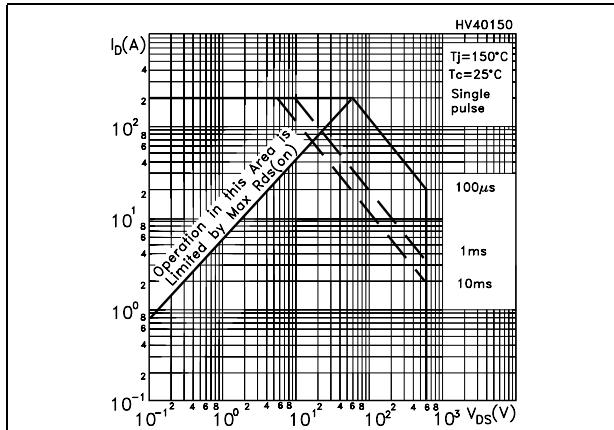


Figure 3. Thermal impedance

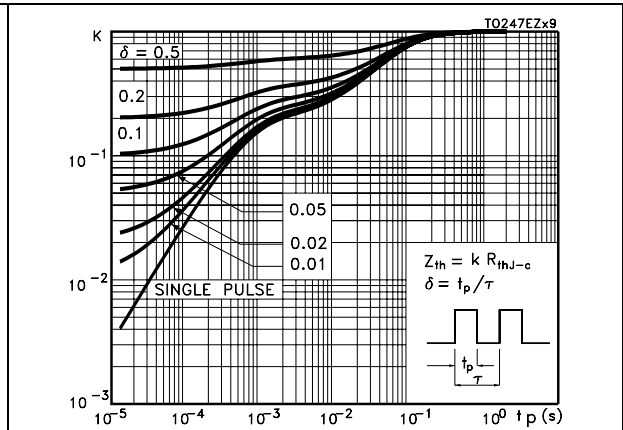


Figure 4. Output characteristics

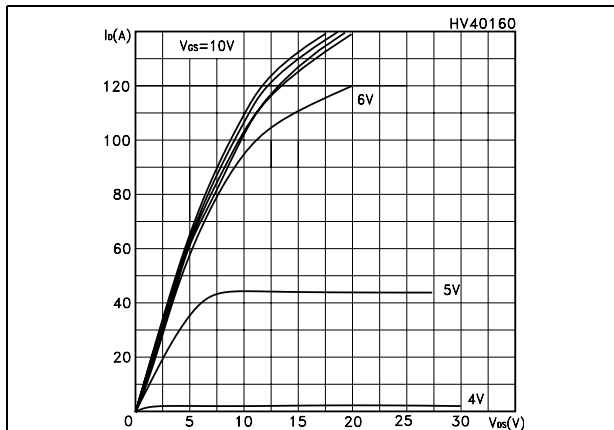


Figure 5. Transfer characteristics

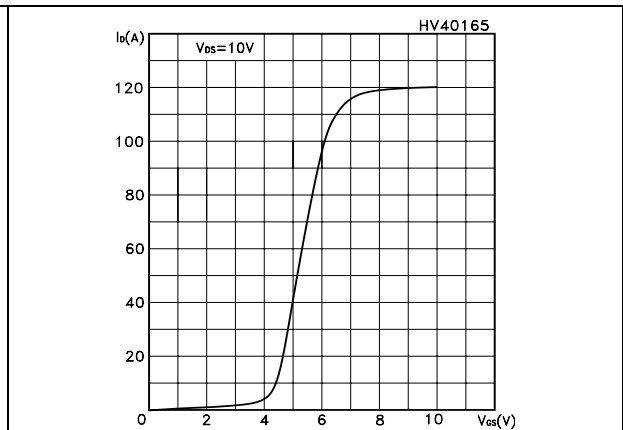


Figure 6. Transconductance

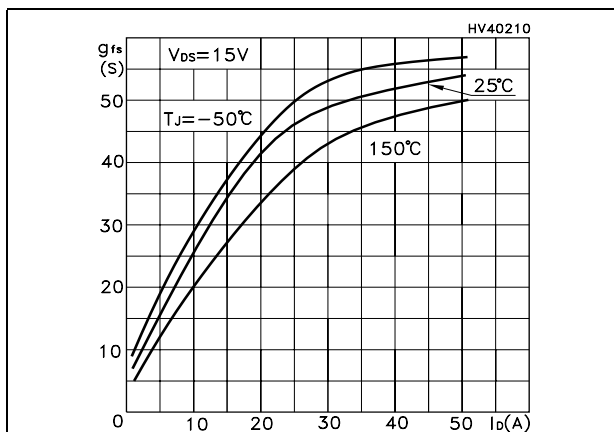


Figure 7. Static drain-source on resistance

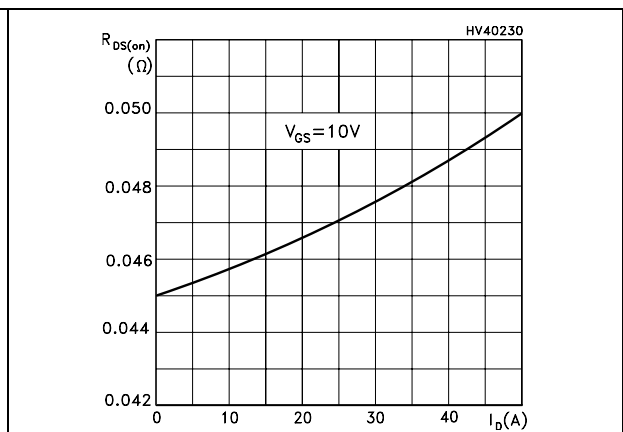


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

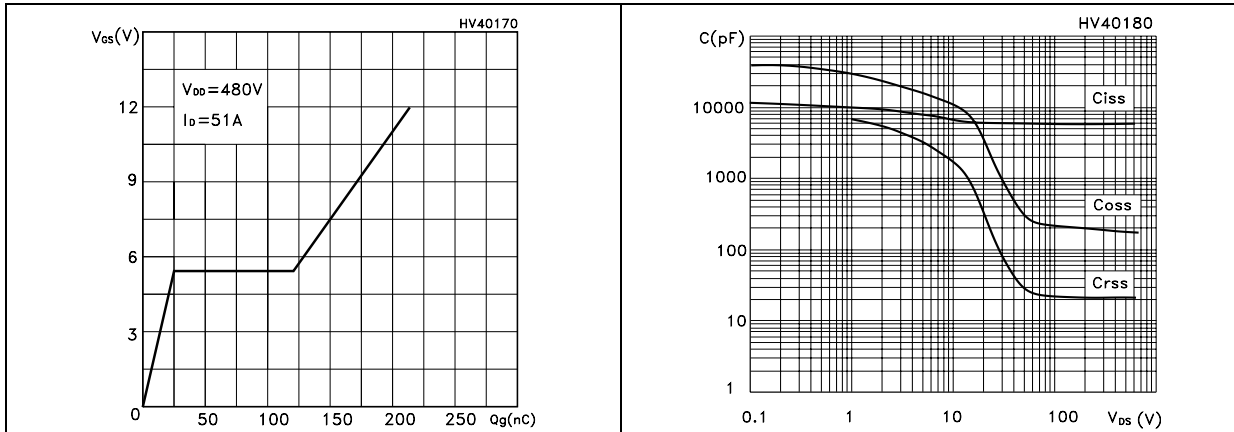


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

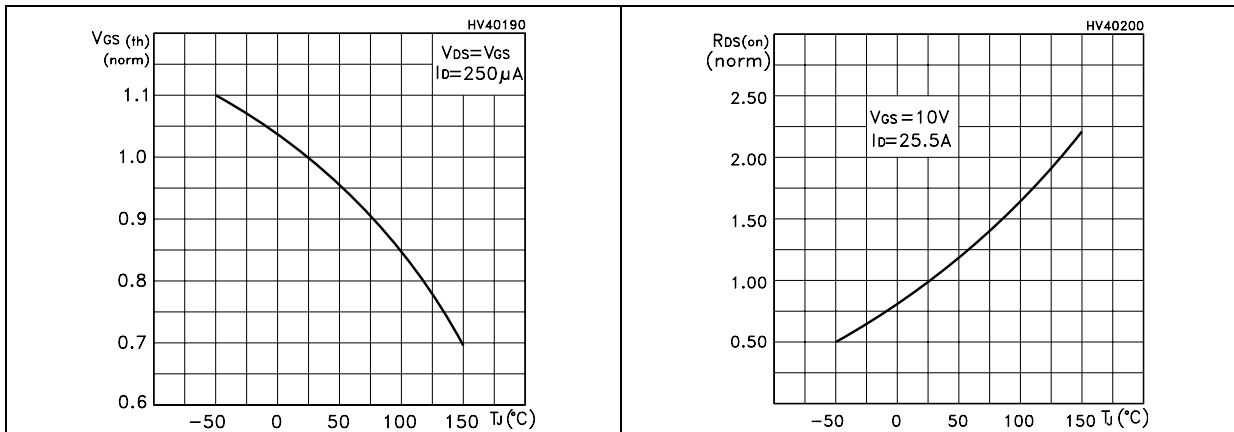
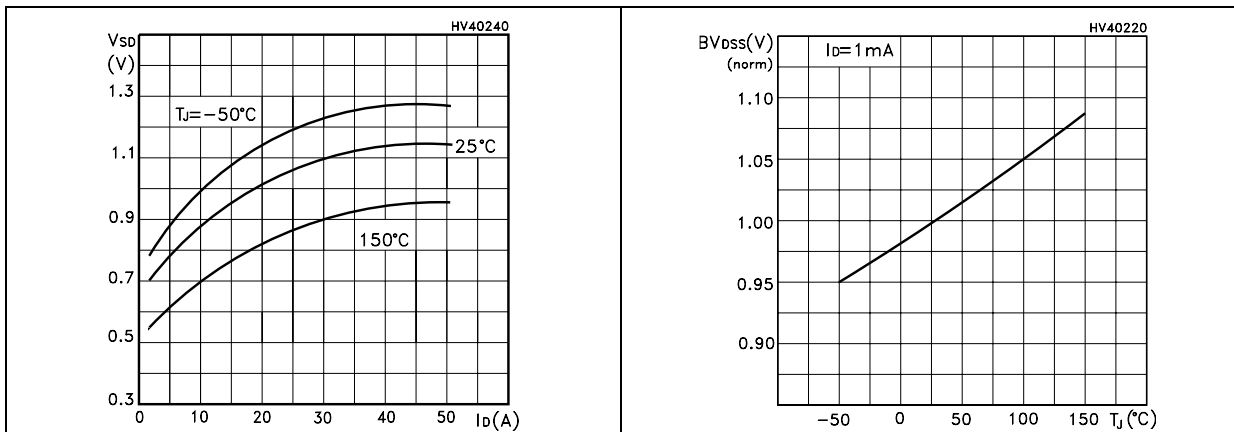


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized $B_{V_{DSS}}$ vs temperature



3 Test circuit

Figure 14. Switching times test circuit for resistive load

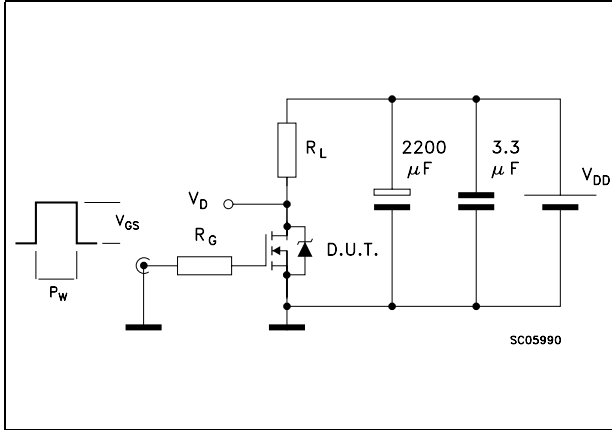


Figure 15. Gate charge test circuit

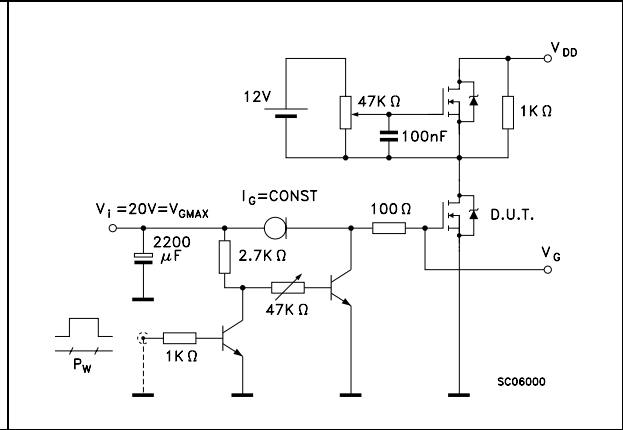


Figure 16. Test circuit for inductive load switching and diode recovery times

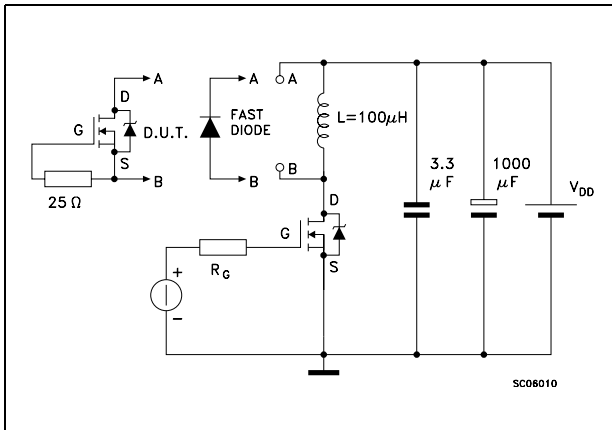


Figure 17. Unclamped inductive load test circuit

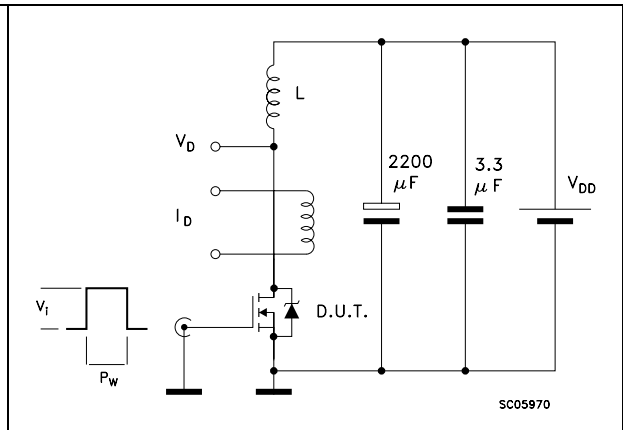


Figure 18. Unclamped inductive waveform

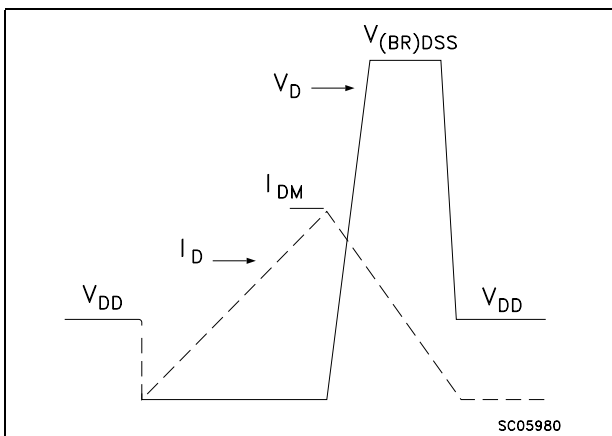
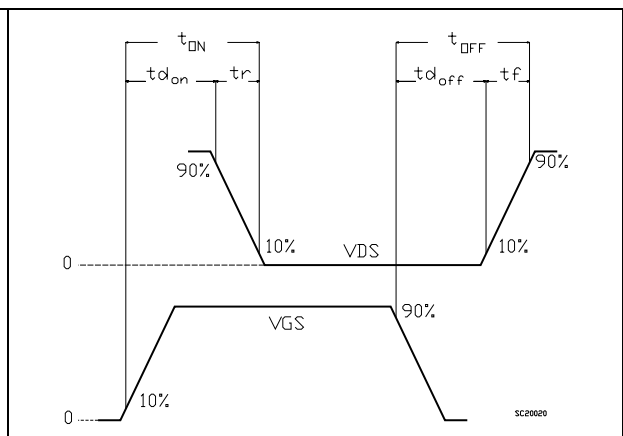


Figure 19. Switching time waveform

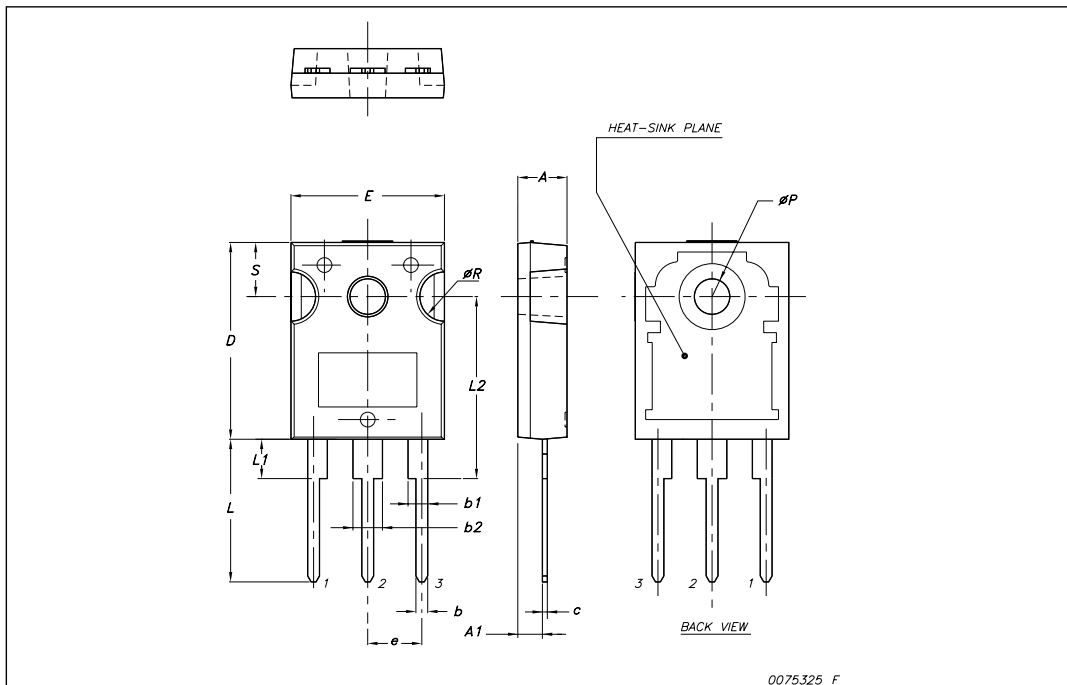


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
06-Nov-2007	1	Initial release
19-Dec-2007	2	<i>Figure 9: Capacitance variations</i> has been updated
16-Jan-2008	3	Document status promoted from preliminary data to datasheet.
31-Jul-2008	4	E _{AS} value has been updated in <i>Table 4</i>

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